

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2014	438/3	USPAT	OR	ON	2004/11/16 17:05
L2	1079	438/243	USPAT	OR	ON	2004/11/16 17:05
L3	906	438/259	USPAT	OR	ON	2004/11/16 17:05
L4	514	438/262	USPAT	OR	ON	2004/11/16 17:05
L5	1032	438/270	USPAT	OR	ON	2004/11/16 17:05
L6	1022	438/386	USPAT	OR	ON	2004/11/16 17:05
S48	0	(ferroelectronic adj polymer) and (interlayer adj dielectric) and trench	USPAT	OR	ON	2004/11/16 16:08
S49	0	(ferroelectric adj polymer) and (interlayer adj dielectric) and trench	USPAT	OR	ON	2004/11/16 16:09
S50	5	(ferroelectric adj polymer) and (interlayer adj dielectric)	USPAT	OR	ON	2004/11/16 16:09
S51	5	S50 and (memory or ILD or oxygen or FPF or FPMD or device or film or trench or via or hole or plug or etch or etching or dielectric or polymer or ferroelectric or metal or substantially or degraded or drgrade or ash or spin or coat or process or barrier or diffusion or evaporation)	USPAT	OR	ON	2004/11/16 17:04

11/16/04